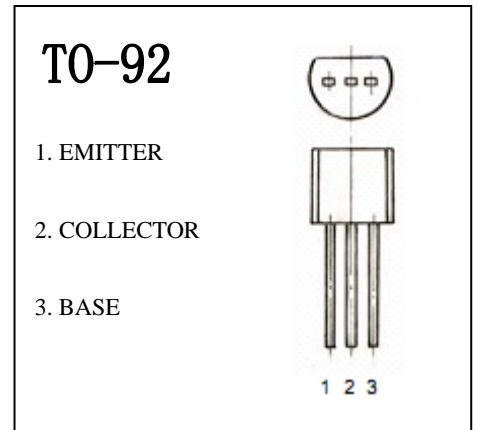


深圳市晶泰源电子有限公司

2SA970 TRANSISTOR(PNP)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-120	V
VCEO	Collector-Emitter Voltage	-120	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current	-0.1	A
PC	Collector Power Dissipation	300	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-120			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-1mA, IB=0	-120			V
Emitter-base breakdown voltage	V(BR)EBO	IC=-100uA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-120V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V, IC=0			-0.1	μA
DC current gain	HFE	Vce=-6V, IC=-2mA	200		700	
Collector-emitter saturation voltage	VCE(sat)	IC=-10mA, IB=-1mA			-0.3	V
Base-emitter voltage	VBE	VCE=-6V, IC=-2mA		-0.65		V
Transition frequency	fT	VCE=-6V, IC=-1mA		100		MHz
Collector output capacitance	Cob	VCB=-10V, IE=0, f=1MHz		4.0		pF

深圳市晶泰源电子有限公司
电话：0755-83211536 传真：0755-83206326
深圳市福田区华强北路华强广场C座11C